
**Polprevodniški elementi - Splošne smernice za kvalifikacijo polprevodnikov - 3.
del: Smernice za načrtovanje ocenjevanja zanesljivosti močnostnega
polprevodniškega modula (IEC 63287-3:2026)**

Semiconductor devices - Generic semiconductor qualification guidelines - Part 3:
Guidelines for reliability qualification plans for power semiconductor module (IEC 63287-3:2026)

Halbleiterbauelemente – Allgemeine Richtlinien zur Halbleiterqualifizierung - Teil 3:
Richtlinien für Zuverlässigkeitsqualifizierungspläne für Leistungshalbleitermodule (IEC 63287-3:2026)

Dispositifs à semiconducteurs - Lignes directrices génériques concernant la qualification
des semiconducteurs - Partie 3: Lignes directrices pour les plans de qualification de la
fiabilité des modules à semiconducteurs de puissance (IEC 63287-3:2026)

Ta slovenski standard je istoveten z: EN IEC 63287-3:2026

ICS:

31.080.01	Polprevodniški elementi (naprave) na splošno	Semiconductor devices in general
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EUROPEAN STANDARD
NORME EUROPÉENNE
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EN IEC 63287-3

September 2026

ICS 31.080.01

English Version

**Semiconductor devices - Generic semiconductor qualification
guidelines - Part 3: Guidelines for reliability qualification plans for
power semiconductor module
(IEC 63287-3:2026)**

Dispositifs à semiconducteurs - Lignes directrices
génériques concernant la qualification des semiconducteurs
- Partie 3: Lignes directrices pour les plans de qualification
de la fiabilité des modules à semiconducteurs de puissance
(IEC 63287-3:2026)

Halbleiterbauelemente - Allgemeine Richtlinien zur
Halbleiterqualifizierung - Teil 3: Richtlinien für
Zuverlässigkeitsqualifizierungspläne für
Leistungshalbleitermodule
(IEC 63287-3:2026)

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EN IEC 63287-3:2026 (E)**European foreword**

The text of document 47/3015/FDIS, future edition 1 of IEC 63287-3, prepared by TC 47 "Semiconductor devices" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN IEC 63287-3:2026.

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IEC 60068-2-1	NOTE	Approved as EN IEC 60068-2-1
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Annex ZA (normative)

Normative references to international publications with their corresponding European publications

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NOTE 1 Where an International Publication has been modified by common modifications, indicated by (mod), the relevant EN/HD applies.

NOTE 2 Up-to-date information on the latest versions of the European Standards listed in this annex is available here: www.cenelec.eu.

<u>Publication</u>	<u>Year</u>	<u>Title</u>	<u>EN/HD</u>	<u>Year</u>
IEC 63287-1	2021	Semiconductor devices - Generic semiconductor qualification guidelines - Part 1: Guidelines for IC reliability qualification	EN IEC 63287-1	2021

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IEC 63287-3

Edition 1.0 2026-08

INTERNATIONAL STANDARD

**Semiconductor devices - Generic semiconductor qualification guidelines -
Part 3: Guidelines for reliability qualification plans for power semiconductor
module**

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**Semiconductor devices -
Generic semiconductor qualification guidelines -
Part 3: Guidelines for reliability qualification plans
for power semiconductor module**

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Draft	Report on voting
47/3015/FDIS	47/3026/RVD

Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

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This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available at www.iec.ch/members_experts/refdocs. The main document types developed by IEC are described in greater detail at www.iec.ch/publications.

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The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under webstore.iec.ch in the data related to the specific document. At this date, the document will be

- reconfirmed,
- withdrawn, or
- revised.

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INTRODUCTION

When performing qualification tests, semiconductor device vendors prepare a specific reliability test plan upon consultation with semiconductor device users in order to efficiently carry out the reliability test.

This guideline presents examples of methods for preparing test plans to determine appropriate reliability test conditions, based on the level of quality required in the operating environments of various applications of power semiconductor modules. As a target of reliability, grades have been specified for each of the following applications: automotive, industrial and consumer electronics. Based on the number of annual operating hours, use period and other parameters assumed for each grade, this guideline defines verification methods for the wear-out failure, and proposes appropriate reliability tests. This guideline defines the concept of quality assurance from early failure to wear-out failure. It also presents approaches to appropriately ensure the reliability of power semiconductor modules.

The test conditions and the acceleration factor values presented in this guideline are only examples used for setting reliability test conditions to verify a required level of quality.

NOTE Qualification tests are tests performed by power semiconductor device vendors, taking into account the quality required by the users of their products.

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